Interface engineering for flexible flash memories

By

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Abstract:

The next-generation electronic systems are expected to be light, flexible and portable for applications in large area displays, integrated circuits (ICs), light emitting diodes (LEDs), radio frequency identification (RFID) tags, solar cells and so on. Memory is an essential part of advanced electronic systems for data processing, storage and communication. Among many types of memories such as ferroelectric, electret, resistive and floating gate [1 & 2] memories, floating gate flash memory devices have gained a great deal of attention due to the simple device structure, non-destructive read-out and controlled charge trap capacity [3-5]. In this presentation, materials and interface engineering for flash memories on plastic substrates will be discussed.

References:


ALL ARE WELCOME

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